

## 1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a TO220F "full pack" plastic package intended for use in applications requiring high bidirectional blocking voltage and high current surge capability with high thermal cycling performance.

## 2. Features and benefits

- High bidirectional blocking voltage capability
- High current surge capability
- High thermal cycling performance
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability

## 3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation

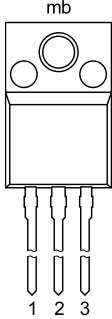

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	800	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_n \leq 69^\circ\text{C}$	-	-	7.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_n \leq 69^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	12	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	120	A
		half sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 8.3\text{ ms}$	-	-	132	A
$T_j$	junction temperature		-	-	125	$^\circ\text{C}$
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	2	15	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125^\circ\text{C}$ ; $R_{GK} = 100\ \Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; <a href="#">Fig. 12</a>	200	1000	-	V/ $\mu\text{s}$
		$V_{DM} = 536\text{ V}$ ; $T_j = 125^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a>	50	130	-	V/ $\mu\text{s}$

### 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
3	G	gate		
mb	n.c.	mounting base; isolated		

### 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT151X-800R	TO220F	BT151X-800R,127	Tube	50	SOT186A	14-Nov-2013
BT151X-800R/DG		BT151X-800R/DG,127	Tube	50	SOT186A (Halogen free)	14-Nov-2013

### 7. Marking

Table 4. Marking codes

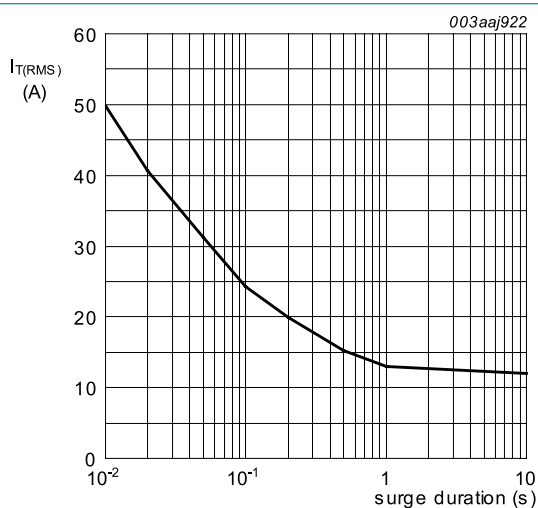
Type number	Marking codes	
	Assembly factory: d	Assembly factory: A
BT151X-800R	BT151X 800R PJdxxxx xx	BT151X 800R PJAxxxx xx
BT151X-800R/DG	BT151X 800RDG PJdxxxx xx	BT151X 800RDG PJAxxxx xx

## 8. Limiting values

**Table 5. Limiting values**

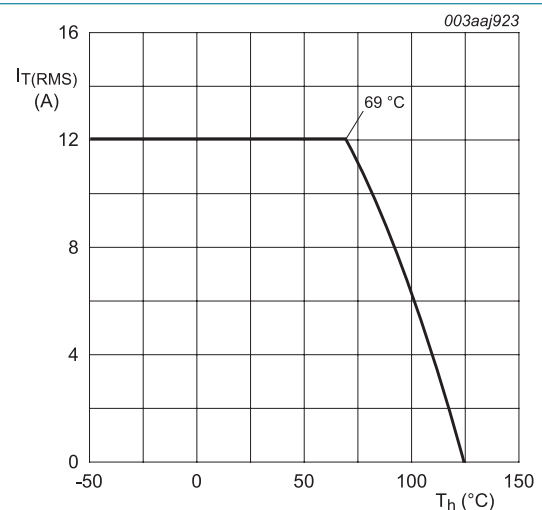
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$V_{RRM}$	repetitive peak reverse voltage		-	800	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_h \leq 69\text{ }^\circ\text{C}$	-	7.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_h \leq 69\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	12	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	120	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 8.3\text{ ms}$	-	132	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	72	A <sup>2</sup> s
$di_T/dt$	rate of rise of on-state current	$I_G = 30\text{ mA}$	-	50	A/ $\mu\text{s}$
$I_{GM}$	peak gate current		-	2	A
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	$^\circ\text{C}$
$T_j$	junction temperature		-	125	$^\circ\text{C}$



$f = 50\text{ Hz}$ ;  $T_h = 69\text{ }^\circ\text{C}$

**Fig. 1. RMS on-state current as a function of surge duration; maximum values**



**Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values**

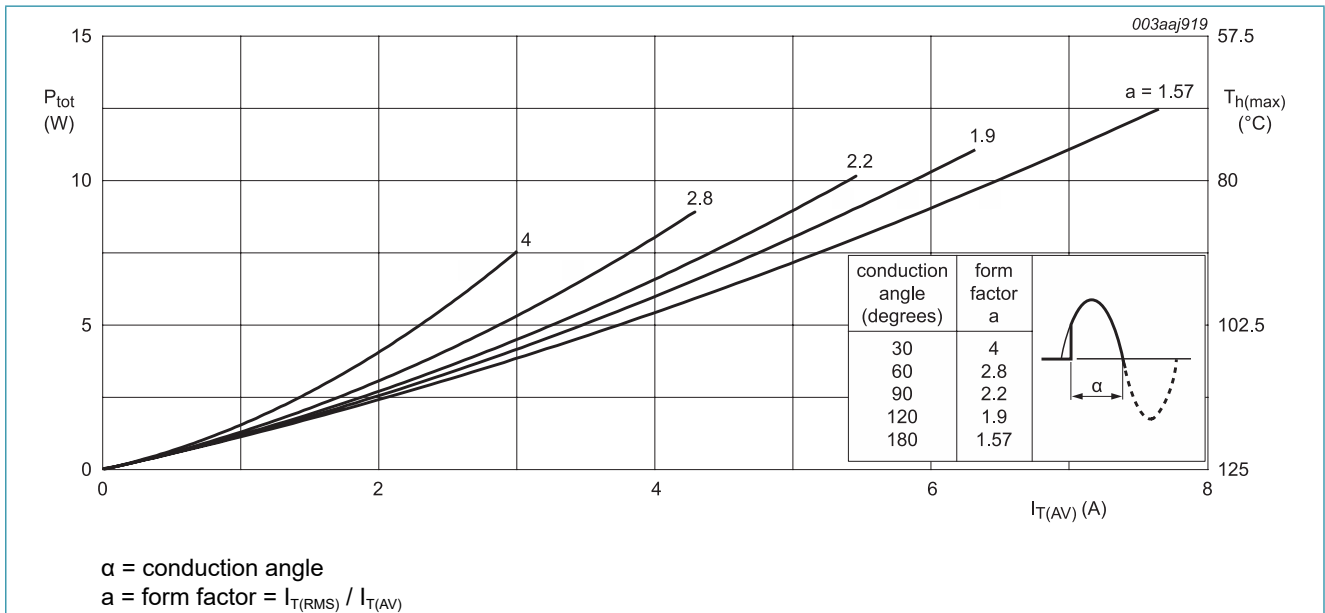


Fig. 3. Total power dissipation as a function of average on-state current; maximum values

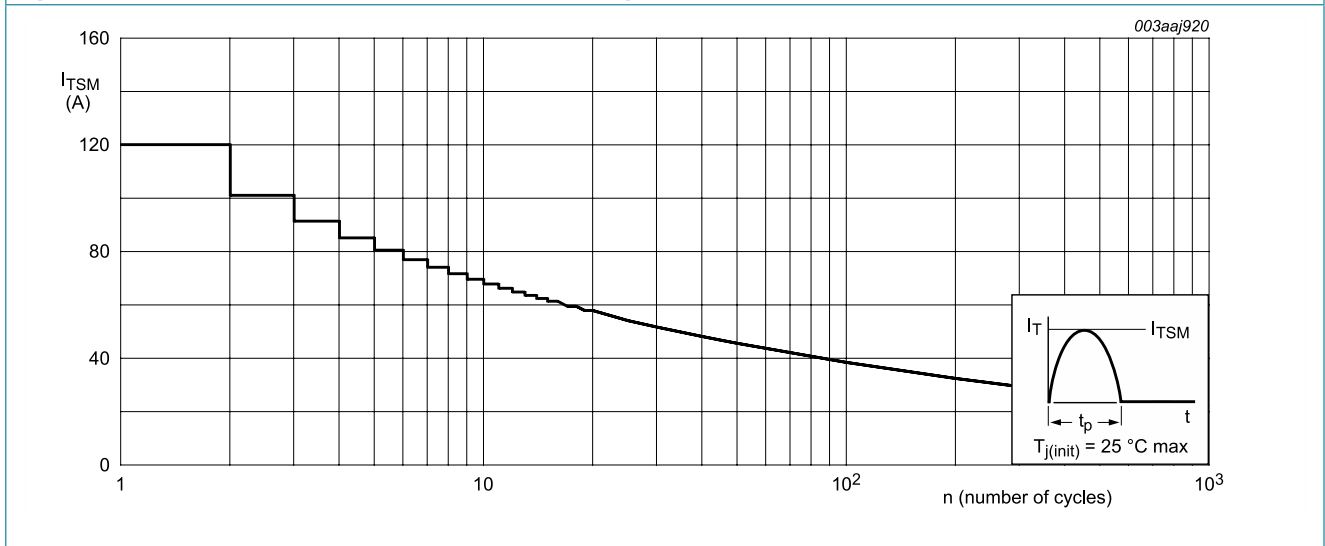
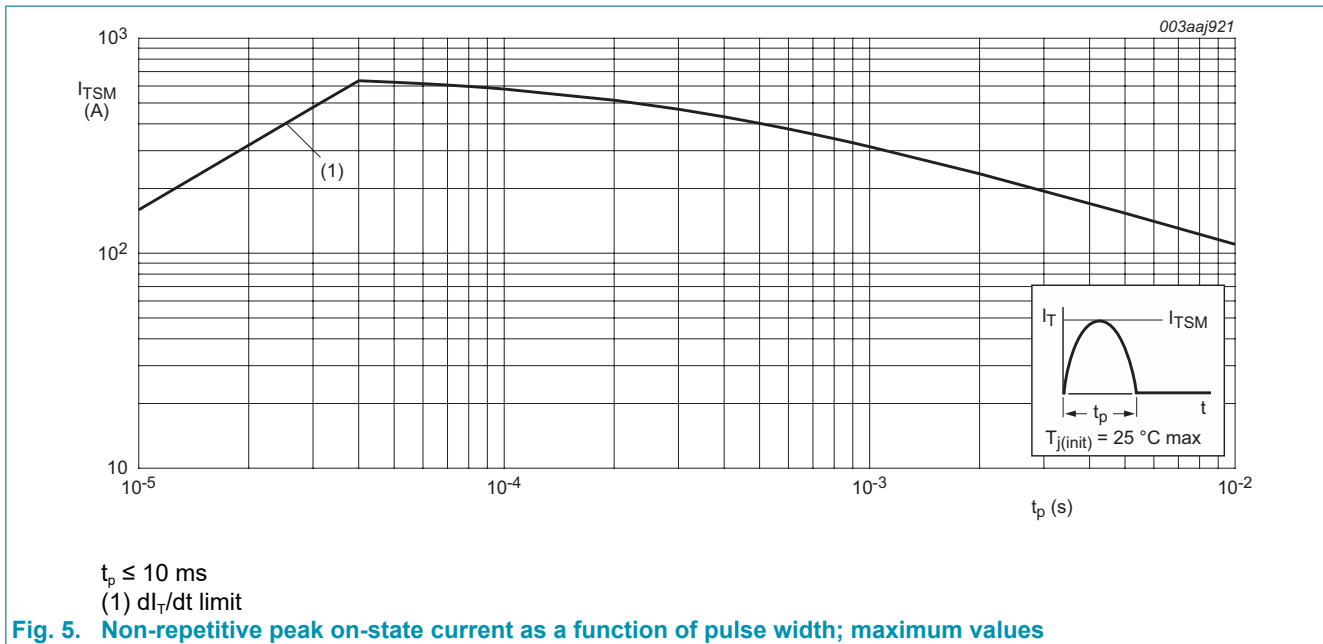


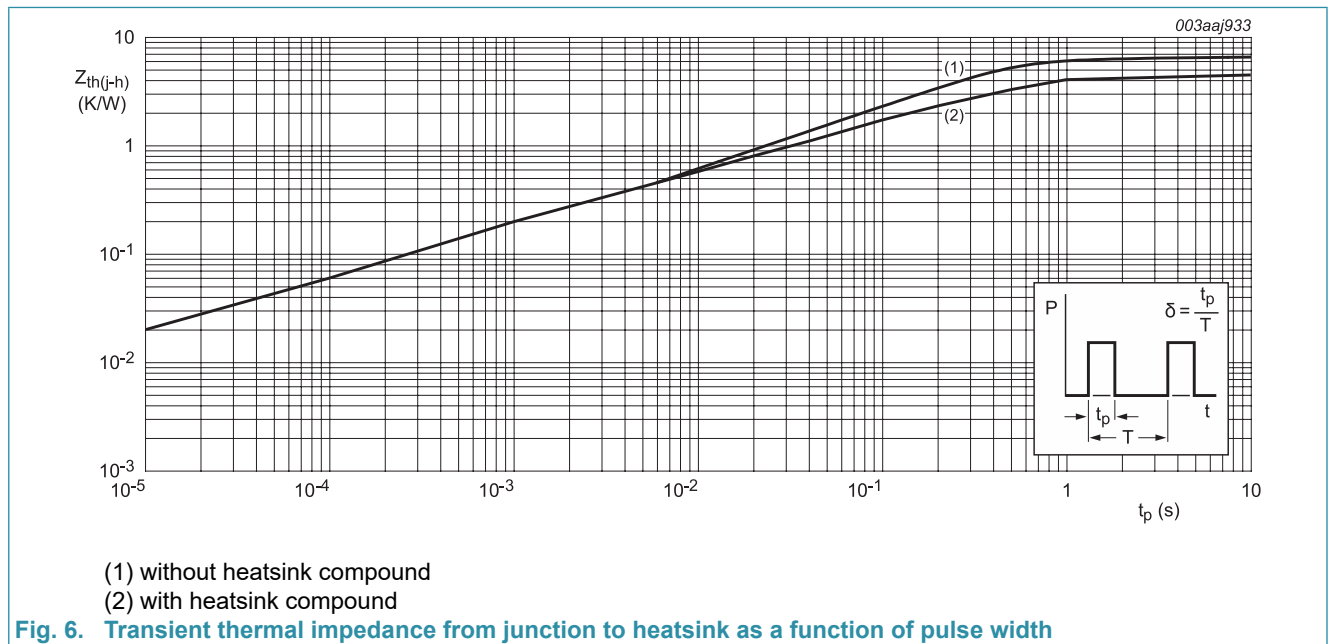
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; <a href="#">Fig. 6</a>	-	-	4.5	K/W
		without heatsink compound; <a href="#">Fig. 6</a>	-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



## 10. Isolation characteristics

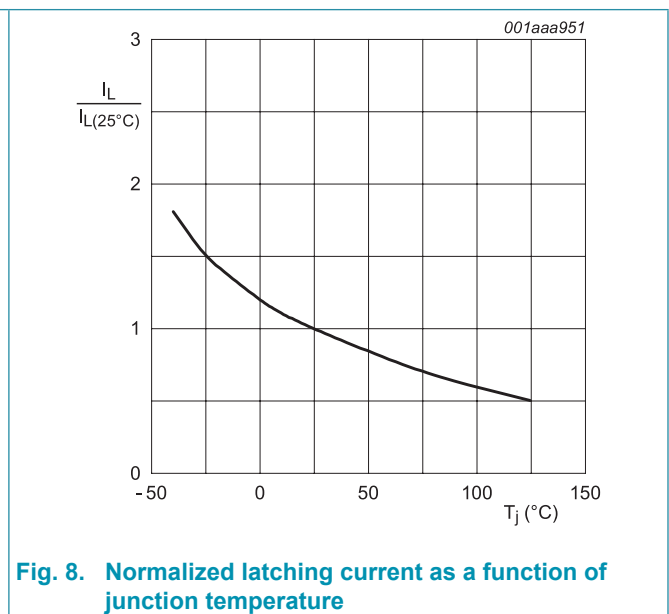
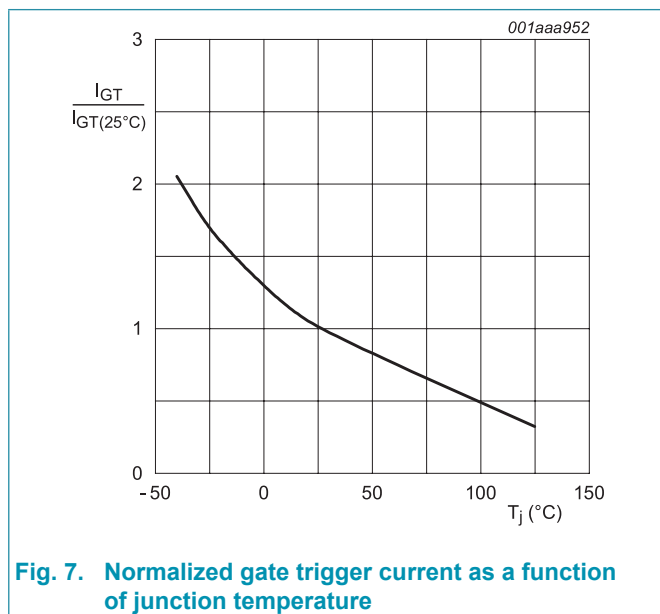
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$ ; $RH \leq 65\%$ ; $T_h = 25\text{ }^\circ\text{C}$	-	-	2500	V
$C_{isol}$	isolation capacitance	from anode to external heatsink; $f = 1\text{ MHz}$ ; $T_h = 25\text{ }^\circ\text{C}$	-	10	-	pF

### 11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 7</a>	-	2	15	mA
$I_L$	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	10	40	mA
$I_H$	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 9</a>	-	7	20	mA
$V_T$	on-state voltage	$I_T = 23\text{ A}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 10</a>	-	1.4	1.75	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	-	0.6	1	V
		$V_D = 800\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C}$	0.25	0.4	-	V
$I_D$	off-state current	$V_D = 800\text{ V}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
$I_R$	reverse current	$V_R = 800\text{ V}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}; T_j = 125\text{ }^\circ\text{C}; R_{GK} = 100\text{ }\Omega;$ ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; <a href="#">Fig. 12</a>	200	1000	-	V/ $\mu$ s
		$V_{DM} = 536\text{ V}; T_j = 125\text{ }^\circ\text{C};$ ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a>	50	130	-	V/ $\mu$ s
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 40\text{ A}; V_D = 800\text{ V}; I_G = 100\text{ mA}; dI_G/dt = 5\text{ A}/\mu\text{s}; T_j = 25\text{ }^\circ\text{C}$	-	2	-	$\mu$ s
$t_q$	commutated turn-off time	$V_{DM} = 536\text{ V}; T_j = 125\text{ }^\circ\text{C}; I_{TM} = 20\text{ A}; V_R = 25\text{ V}; (dI_T/dt)_M = 30\text{ A}/\mu\text{s}; dV_D/dt = 50\text{ V}/\mu\text{s}; R_{GK(ext)} = 100\text{ }\Omega;$ ( $V_{DM} = 67\%$ of $V_{DRM}$ )	-	70	-	$\mu$ s



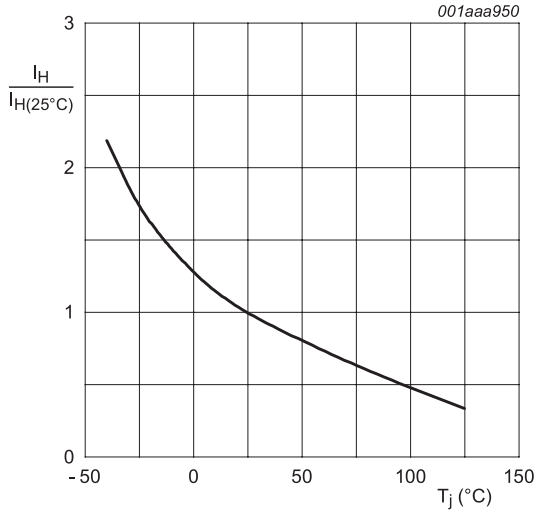
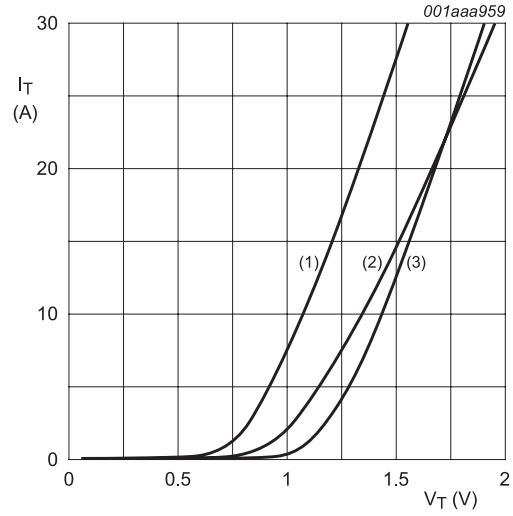


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.06 \text{ V}; R_s = 0.0304 \Omega$   
 (1)  $T_j = 125 \text{ }^\circ\text{C}$ ; typical values  
 (2)  $T_j = 125 \text{ }^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage

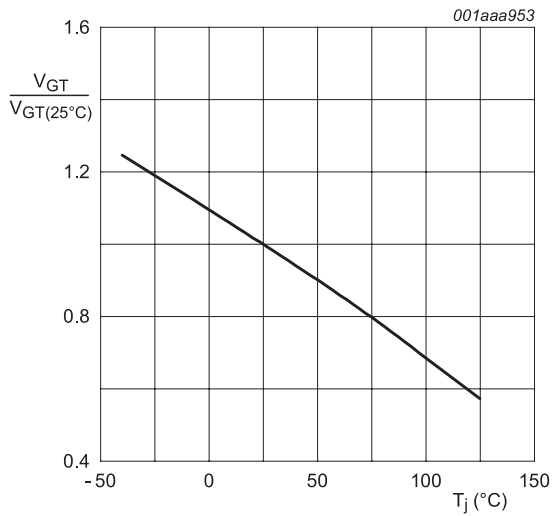
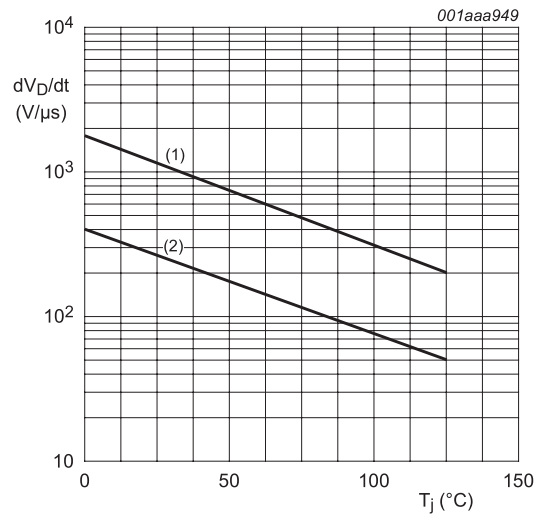


Fig. 11. Normalized gate trigger voltage as a function of junction temperature



(1)  $R_{GK} = 100 \Omega$ ;  
 (2) gate open circuit

Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

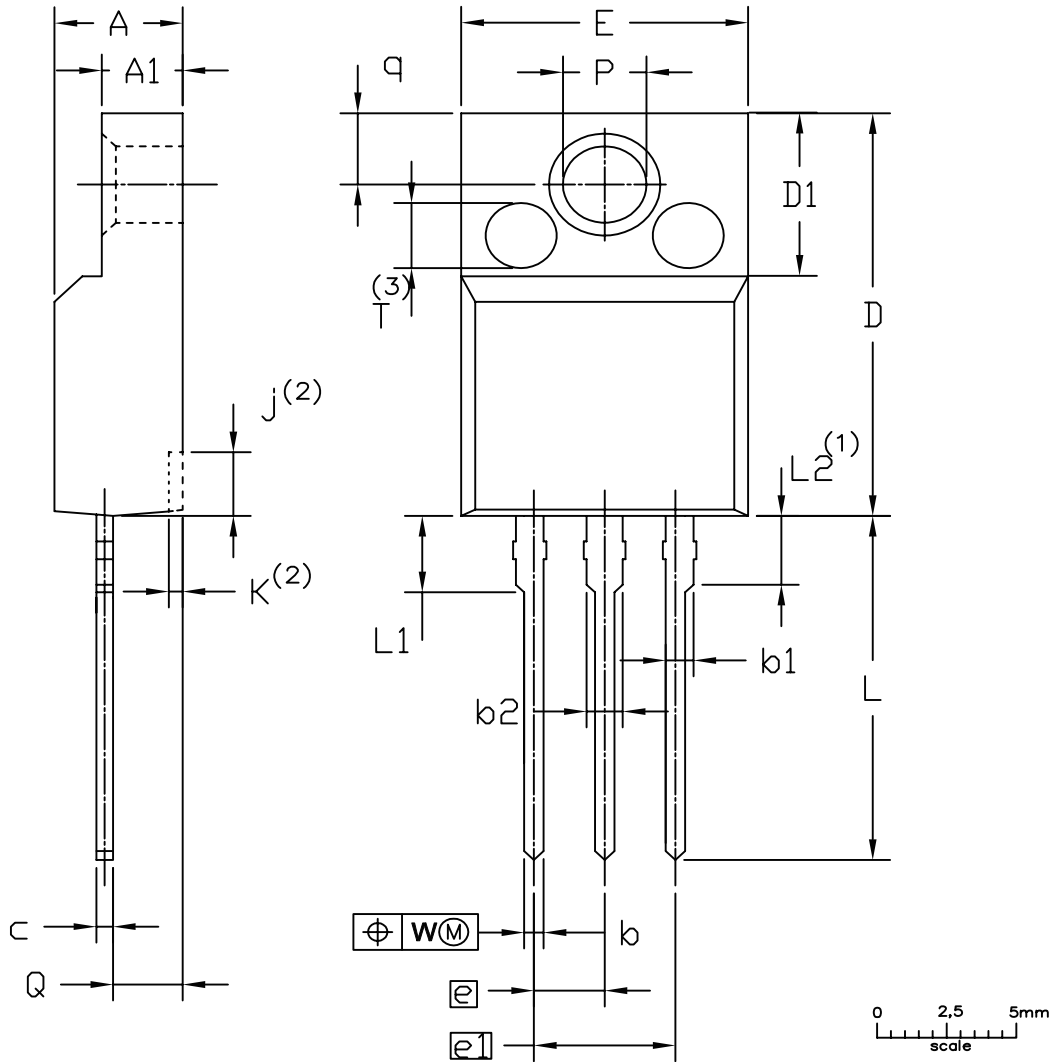


### 12. Package outline

Assembly factory: d & A

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"

SOT186A



UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	c	D	D <sub>1</sub>	E	e	e <sub>1</sub>	j <sup>(2)</sup>	k <sup>(2)</sup>	L	L <sub>1</sub>	L <sub>2</sub> <sup>(1)</sup> max.	P	Q	q	W	T <sup>(3)</sup>
mm	4.6	2.9	0.9	1.1	1.4	0.7	15.8	6.5	10.3	2.54	5.08	2.7	0.6	14.4	3.30	3	3.2	2.6	3.0	0.4	2.5
	4.0	2.5	0.7	0.9	1.0	0.4	15.2	6.3	9.7			1.7	0.4	13.5	2.79		3.0	2.3	2.6		

- Notes
- Terminal dimensions within this zone are uncontrolled
  - Dot lines area designs may vary
  - Eject pin mark is for reference only

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT186A		3 LEADS TO220F			2013-11-14

## 13. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 25 September 2024

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